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CORRECTION

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Correction for 'Hafnium–zirconium oxide interface models with a semiconductor and metal for ferroelectric devices' by Kisung Chae *et al.*, *Nanoscale Adv.*, 2021, DOI: 10.1039/d1na00230a.

The authors regret that an incorrect version of Fig. 7 was included in the original article. The correct version of Fig. 7 is presented below.

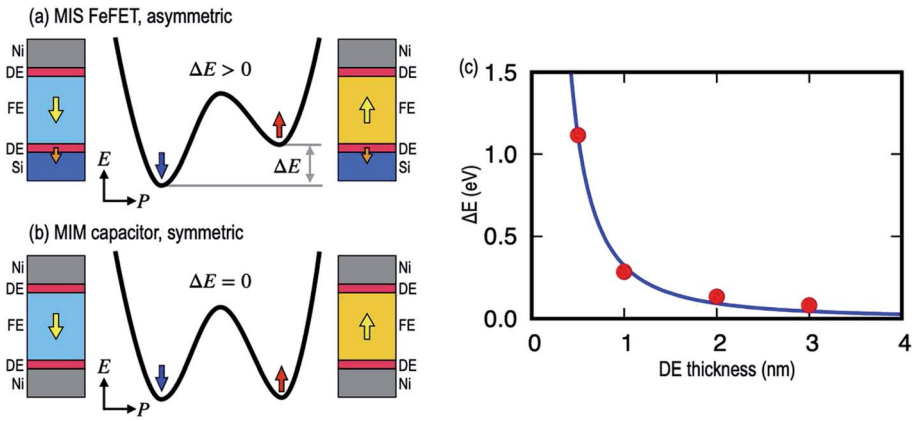

Fig. 7 Total energy landscape in MIM and MIS devices. Schematic diagram of energy landscapes as a function of polarization state for (a) an asymmetric MIS FeFET and (b) a symmetric MIM capacitor. (c) The energy difference (Δ*E*) as a function of DE thickness in MIS with the FE thickness fixed at 2 nm.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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